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SEMICONDUCTOR



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PLED

3N06-MS

Product specification

DESCRIPTION

The 3N06-MS uses advanced trench technology to provide excellent $R_{DS(on)}$, low gate charge and operation with gate voltage as low as 2.5V.

This device is suitable for use as a battery protection or in other switching application.

3N06-MS N-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_b
60V	105mΩ@10V	3A
	125mΩ@4.5V	

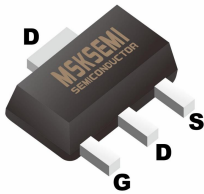
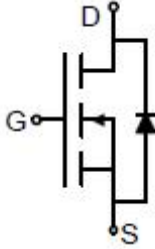

FEATURE

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

APPLICATION

- Battery Switch
- DC/DC Converter

Reference News

PACKAGE OUTLINE	PIN CONFIGURATION	Marking
 <p>SOT-89</p>		

Maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	3	A
Pulsed Drain Current (note 1)	I _{DM}	10	A
Power Dissipation	P _D	0.35	W
Thermal Resistance from Junction to Ambient (note 2)	R _{θJA}	357	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~+150	°C

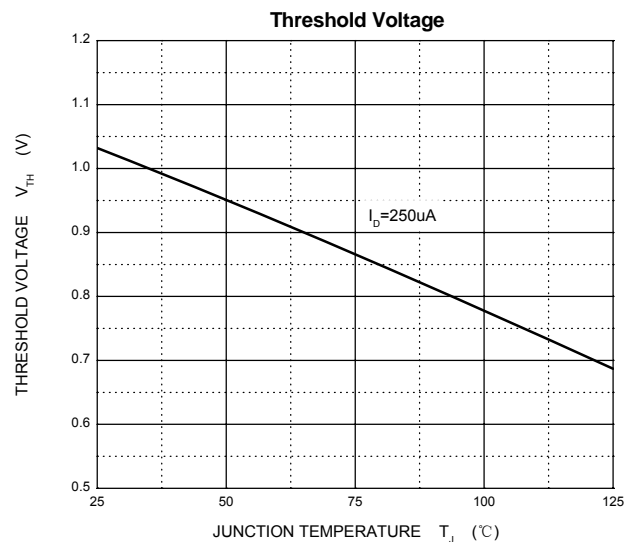
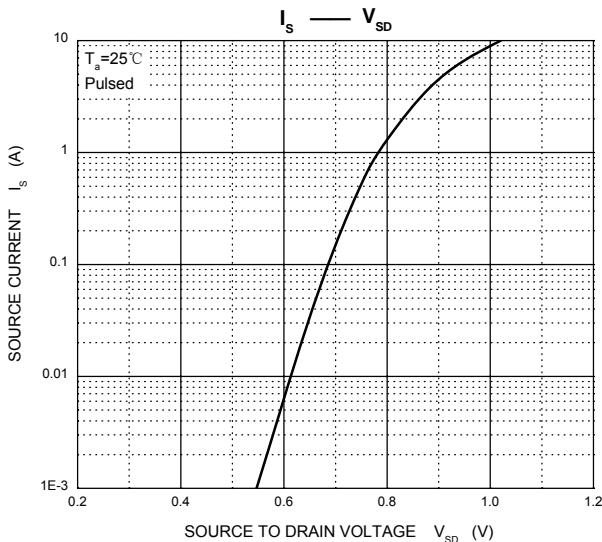
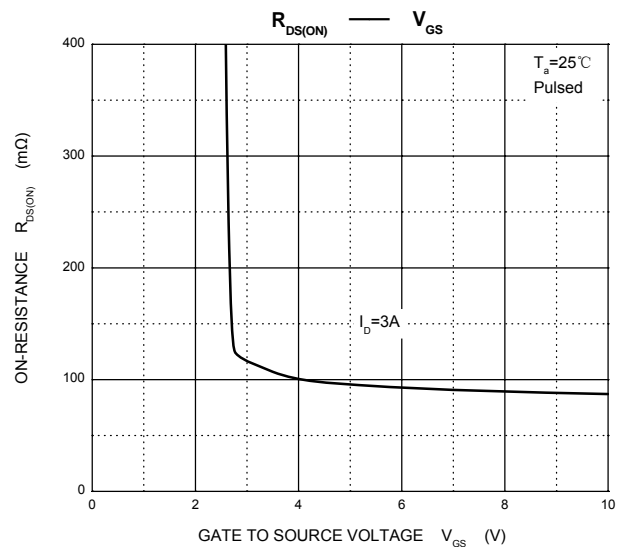
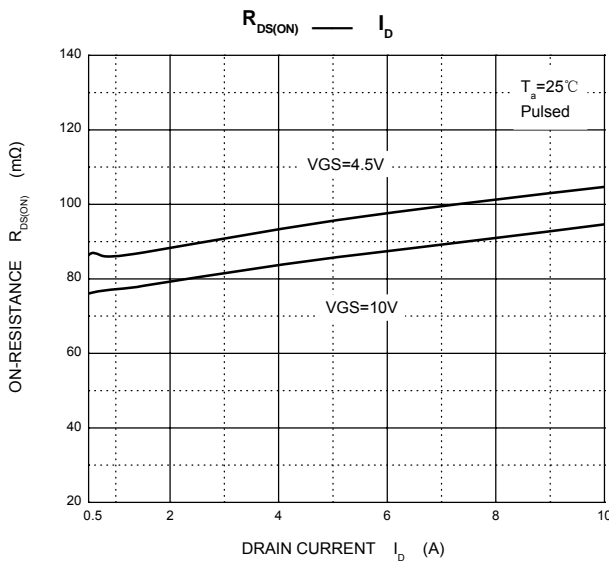
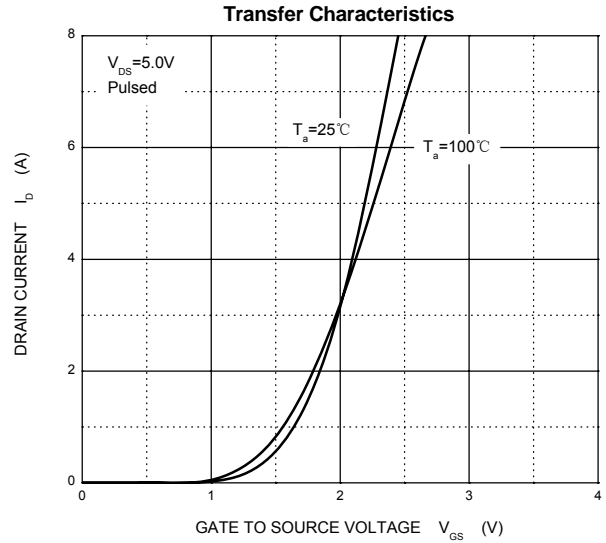
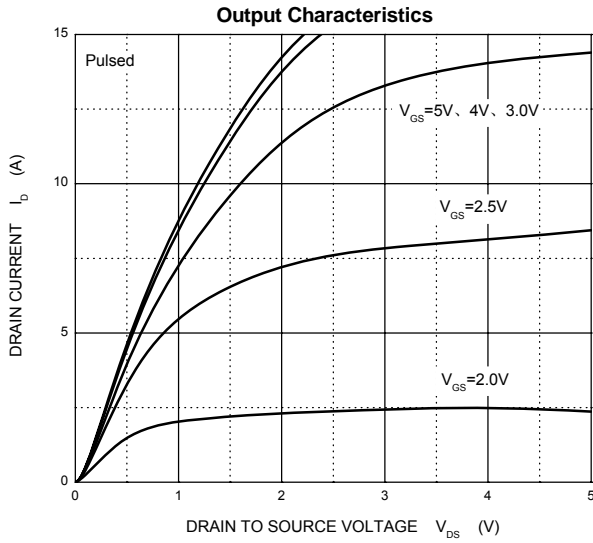
MOSFET ELECTRICAL CHARACTERISTICS Ta =25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	60			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =60V, V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} = 0V			±100	nA
Gate threshold voltage (note 3)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.5		2	V
Drain-source on-resistance (note 3)	R _{DS(on)}	V _{GS} =10V, I _D =3A			105	mΩ
		V _{GS} =4.5V, I _D =3A			125	mΩ
Forward tranconductance (note 3)	g _{FS}	V _{DS} =15V, I _D =2A	1.4			S
Diode forward voltage (note 3)	V _{SD}	I _S =3A, V _{GS} = 0V			1.2	V
DYNAMIC CHARACTERISTICS (note 4)						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, f =1MHz		247		pF
Output Capacitance	C _{oss}			34		pF
Reverse Transfer Capacitance	C _{rss}			19.5		pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time	t _{d(on)}	V _{GS} =10V, V _{DD} =30V, I _D =1.5A, R _{GEN} =1Ω		6		ns
Turn-on rise time	t _r			15		ns
Turn-off delay time	t _{d(off)}			15		ns
Turn-off fall time	t _f			10		ns
Total Gate Charge	Q _g	V _{DS} =30V, V _{GS} =4.5V, I _D =3A		6		nC
Gate-Source Charge	Q _{gs}			1		nC
Gate-Drain Charge	Q _{gd}			1.3		nC

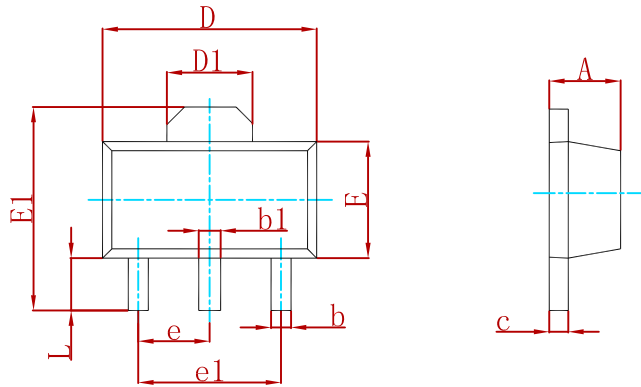
Notes :

1. Repetitive rating : Pulse width limited by junction temperature.
2. Surface mounted on FR4 board , t≤10s.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle≤0.5%.
4. Guaranteed by design, not subject to producing.

Typical Characteristics

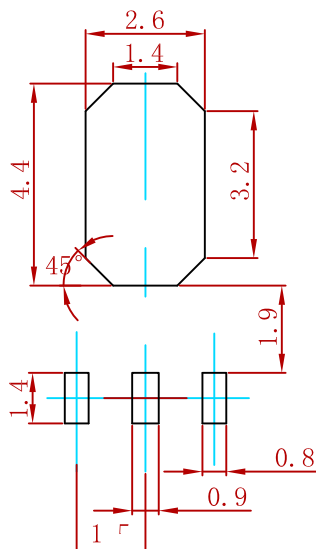


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
3N06-MS	SOT-89	1000

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